

# N-channel TrenchMOS FET Rev. 01 — 4 October 2010

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V and 24 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	75	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u>	-	-	33	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	80	W
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{}$	-	24.5	29	mΩ
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 33$ A; $V_{sup} \le 75$ V; $R_{GS} = 50$ $\Omega$ ; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped	-	-	42	mJ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 60 V; $V_{GS}$ = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	9.4	-	nC



**N-channel TrenchMOS FET** 

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		G (EA)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6226-75C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Cymbol	Doromotor	Conditions		Min	May	Linit
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	75	V
$V_{GS}$	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
$I_D$	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>		-	33	Α
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>		-	23	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see Figure 3		-	130	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	80	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain of	diode					
Is	source current	T <sub>mb</sub> = 25 °C		-	33	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \mu\text{s}; \text{ pulsed};  T_{\text{mb}} = 25 ^{\circ}\text{C}$		-	130	Α
Avalanche rug	gedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 33 A; $V_{sup} \le 75$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	42	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy		[3][4][5]	-	-	J

<sup>[1] -16</sup>V accumulated duration not to exceed 168 hrs.

<sup>[2]</sup> Accumulated pulse duration not to exceed 5 mins.

<sup>[3]</sup> Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

<sup>[4]</sup> Repetitive avalanche rating limited by an average junction temperature of 170 °C.

<sup>[5]</sup> Refer to application note AN10273 for further information.

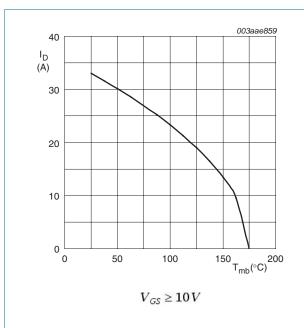


Fig 1. Continuous drain current as a function of mounting base temperature

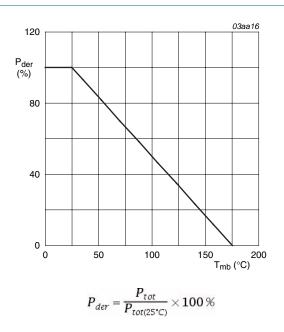
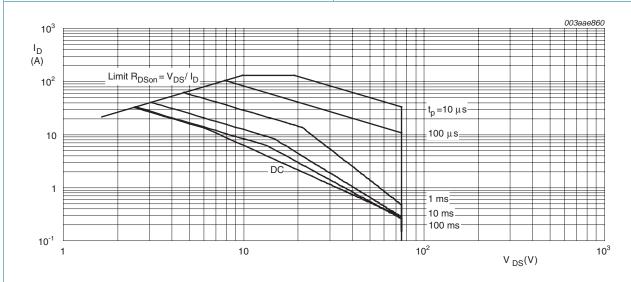


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb}$  = 25 °C;  $I_{DM}$ is a single pulse

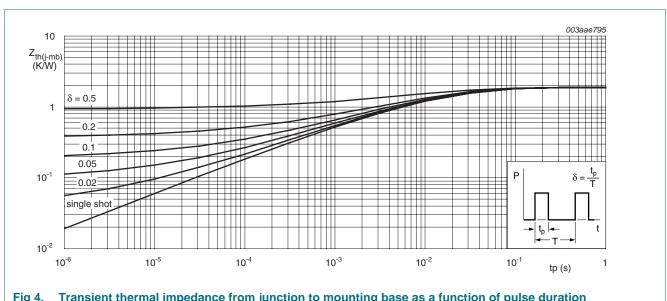
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

**N-channel TrenchMOS FET** 

### **Thermal characteristics**

Table 5. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.87	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

### 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	75	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	68	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see Figure 9	-	-	3.3	3.3 V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 9	0.8	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS}$ = 75 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	1	μΑ
$I_{GSS}$	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nΑ
		$V_{DS}$ = 0 V; $V_{GS}$ = -20 V; $T_j$ = 25 °C	-	2	100	nΑ
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	24.5	29	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 12 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11	-	30	40	mΩ
		$V_{GS} = 5 \text{ V; } I_D = 12 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	28	35	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_j = 175 °C;$ see Figure 12; see Figure 11	-	-	75.4	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 60 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 13; see Figure 14	-	34	-	nC
		$I_D = 25 \text{ A}$ ; $V_{DS} = 60 \text{ V}$ ; $V_{GS} = 5 \text{ V}$ ; see Figure 13; see Figure 14	-	18.6	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 10 \text{ V};$	-	5.6	-	nC
$Q_{GD}$	gate-drain charge	see Figure 13; see Figure 14	-	9.4	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1500	2000	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	128	155	pF
C <sub>rss</sub>	reverse transfer capacitance		-	89	110	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 55 \text{ V}; R_L = 2.2 \Omega; V_{GS} = 10 \text{ V};$	-	11.8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$	-	15.6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	59	-	ns
t <sub>f</sub>	fall time		-	31	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_j = 25  ^{\circ}\text{C}$	-	7.5	-	nΗ

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 16	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}$	-	42	-	ns
Q <sub>r</sub>	recovered charge		-	74	-	nC

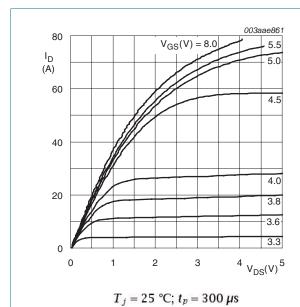


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

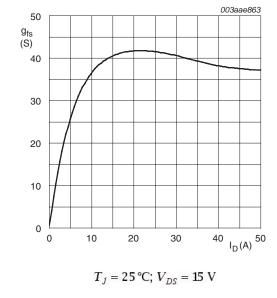


Fig 6. Forward transconductance as a function of drain current; typical values

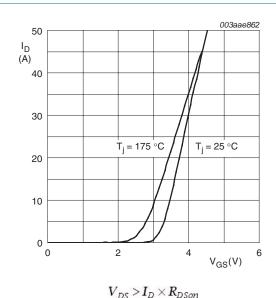


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

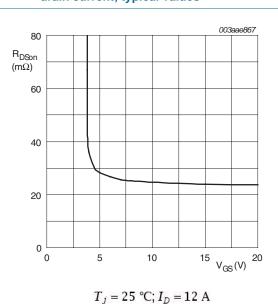


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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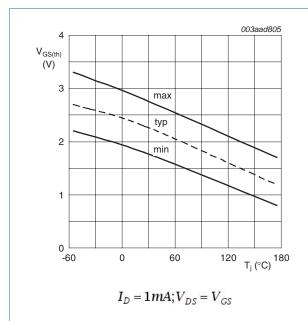


Fig 9. Gate-source threshold voltage as a function of junction temperature

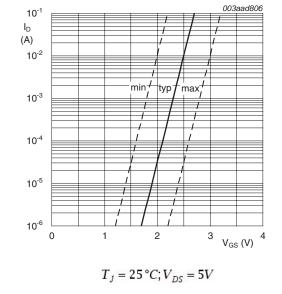


Fig 10. Sub-threshold drain current as a function of gate-source voltage

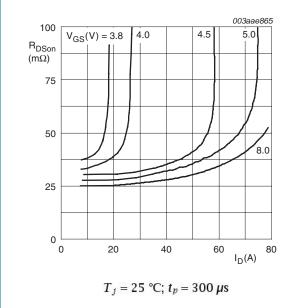


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

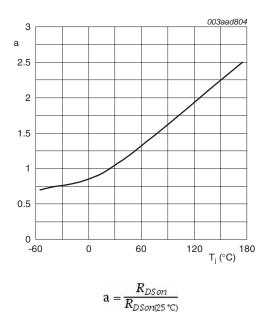
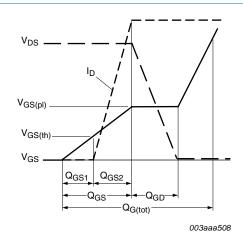


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

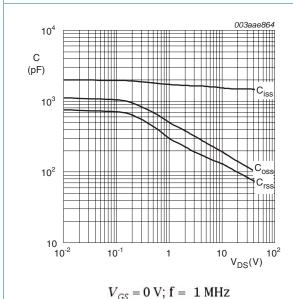


10 003aae866 (V) 7.5 14V V<sub>DS</sub>= 60V 2.5 Q<sub>G</sub>(nC) 40

 $T_j = 25$  °C;  $I_D = 25$  A

Fig 13. Gate charge waveform definitions

Fig 14. Gate-source voltage as a function of gate charge; typical values



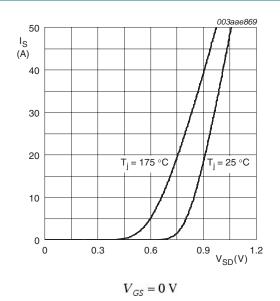


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### 7. Package outline

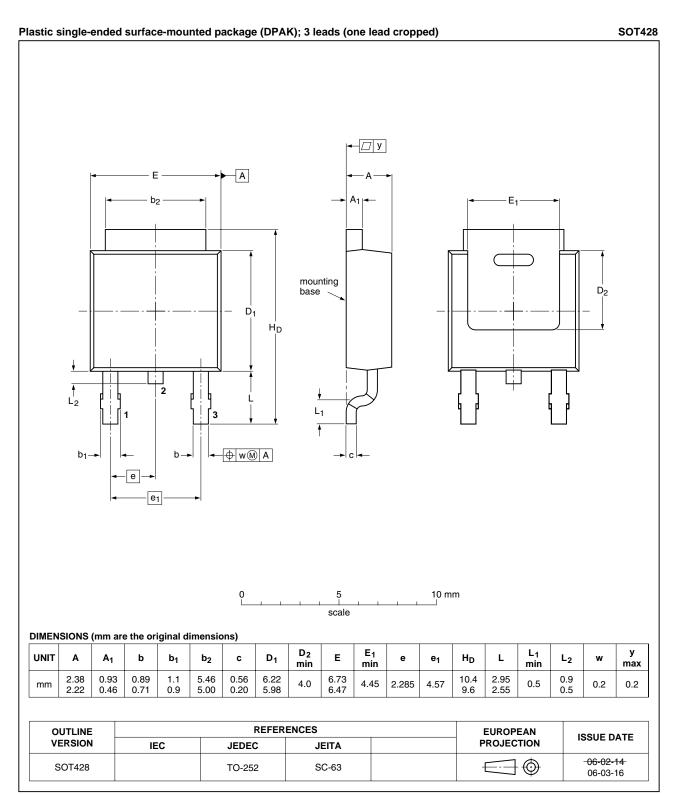


Fig 17. Package outline SOT428 (DPAK)

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# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6226-75C v.1	20101004	Product data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2] Product status[3]		Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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